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CLAIMS 1-31 (CANCELLED)

32. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device, comprising the steps of:

(a) forming two or more element forming regions over a surface portion of a semiconductor substrate, said two or more element forming regions being defined by an insulating film and each extending in a first direction and being arranged in a second direction perpendicular to said first direction;

(b) forming a plurality of memory cells over main surfaces of said two or more element forming regions; and

(c) forming a conductive film over said semiconductor substrate, said conductive film having a first portion which extends in said first direction along a first side of said surface portion of said semiconductor substrate and a second portion which extends in said second direction along a second side of said surface portion so as to surround said plurality of memory cells,

wherein said element forming regions extend up to have end portions positioned below said second portion of said conductive film, which extends in said second direction.

33. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device according to claim 32, wherein said step (b) includes:

- (b₁) forming a first electrode ~~through~~over a first insulating film on one of said element forming regions;
- (b₂) forming a second electrode ~~through~~over a second insulating film on said first electrode, said second electrode extending in said second direction; and
- (b₃) forming semiconductor regions in ~~the~~said one element forming region on both sides of said second electrode.

34. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 32,

wherein said memory cells are non-volatile memory cells.

35. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device, comprising the steps of:

- (a) forming two or more element forming regions over a surface portion of a semiconductor substrate, said two or more element forming regions being defined by an insulating

film and each extending in a first direction and being arranged in a second direction perpendicular to said first direction;

(b) forming a plurality of memory cells over main surfaces of said ~~two-or-more~~ element forming regions; and

(c) forming a conductive film over said ~~surface~~ of a semiconductor substrate, said conductive film having at least a portion extending in said second direction,

wherein said element forming regions extend ~~up to~~ have end portions positioned below said portion of said conductive film.

36. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device according to claim 35, wherein said step (b) includes:

(b₁) forming a first electrode ~~through~~ over a first insulating film on one of said element forming regions;

(b₂) forming a second electrode ~~through~~ over a second insulating film on said first electrode, said second electrode extending in said second direction; and

(b₃) forming semiconductor regions in the said one element forming region on both sides of said second electrode.

37. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 36,

wherein said memory cells are non-volatile memory cells.

38. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device comprising steps of:

(a) forming element isolation regions in a semiconductor substrate so as to provide two or more element forming regions over a surface of said semiconductor substrate;

(b) forming a plurality of memory cells over main surfaces of said two or more element forming regions; and

(c) forming a ~~conductive film~~ conductive film over said semiconductor substrate, ~~said conductive film extending to below said two or more element forming regions,~~

wherein said element forming regions extend in a first direction, and

wherein said conductive film has at least a portion extending in a second direction, perpendicular to said first direction, and disposed over end portions of said element forming regions.

39. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 38, wherein said step (a) includes:

- (a₁) forming grooves in said semiconductor substrate; and
- (a₂) depositing an insulating film in said grooves.

40. (Currently Amended) A method of manufacturing a semiconductor integrated circuit device according to claim 38, wherein said step (b) includes:

- (b₁) forming a first electrode ~~through~~over a first insulating film on one of said element forming regions;
- (b₂) forming a second electrode ~~through~~over a second insulating film on said first electrode; and
- (b₃) forming semiconductor regions in the said one element forming region on both sides of said second electrode.

41. (Previously Presented) A method of manufacturing a semiconductor integrated circuit device according to claim 38,

wherein said memory cells are non-volatile memory cells.

42. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 32, wherein said insulating film of step (a) is formed by a process comprising the steps of:

(a₁) forming grooves in said semiconductor substrate;
and

(a₂) depositing insulating material in said grooves.

43. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 35, wherein said insulating film of step (a) is formed by a process comprising the steps of:

(a₁) forming grooves in said semiconductor substrate;
and

(a₂) depositing insulating material in said grooves.

44. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 32, wherein memory cells formed on an outermost element forming region of said element forming regions do not function as memory cells.

45. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 35, wherein memory cells formed on an outermost element forming region of said element forming regions do not function as memory cells.

46. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 38, wherein memory cells formed on an outermost element forming region of said element forming regions do not function as memory cells.

47. (New) A method of manufacturing a semiconductor integrated circuit device, comprising the steps of:

- (a) forming grooves in a semiconductor substrate;
- (b) depositing insulating material in said grooves to define two or more element forming regions over a surface portion of said substrate, said element forming regions extending in a first direction and being arranged in a second direction perpendicular to said first direction;
- (c) forming a plurality of memory cells over main surfaces of said element forming regions; and
- (d) forming a conductive film over said semiconductor

substrate, said conductive film having a first portion which extends in said first direction along a first side of said surface portion of said substrate, and a second portion which extends in said second direction along a second side of said surface portion and which is disposed over end portions of said element forming regions.

48. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 47, wherein said step (c) includes:

(c₁) forming a first electrode on a first insulating film over one of said element forming regions;

(c₂) forming a second electrode on a second insulating film over said first electrode; and

(c₃) forming semiconductor regions in said one element forming region on both sides of said second electrode.

49. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 47, wherein said memory cells are non-volatile memory cells.

50. (New) A method of manufacturing a semiconductor integrated circuit device according to claim 47, wherein memory cells formed on an outermost element forming region

of said element forming regions do not function as memory cells.

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